

IN THE CLAIMS:

Claims 1-29 (Canceled)

30. (New Claim) An integrated circuit device comprising:

a metallization interconnect system overlying a semiconductor substrate, the metallization interconnect system including at least a first and a second interconnect feature located within a dielectric layer;

a bond pad level overlying the metallization interconnect system, the bond pad level comprising a contact pad and at least a portion of a second interconnect structure, wherein:

the contact pad is configured for connection external to the integrated circuit device and is in contact with the first interconnect feature; and

the second interconnect structure forms a single conductive feature with the contact pad and is in contact with the second interconnect feature;

a passivation layer overlying at least a portion of the bond pad level to expose the contact pad and protect the second interconnect structure.

31. (New Claim) The integrated circuit device of claim 30 wherein the second interconnect structure is a power bus.

32. (New Claim) The integrated circuit device of claim 30 wherein a plane of an upper surface of the contact pad is not coplanar with a plane of an upper surface of the second

interconnect structure

33. (New Claim) The integrated circuit device of Claim 32 wherein the plane of the second interconnect structure is above the plane of the contact pad.

34. (New Claim) The integrated circuit device of claim 30 wherein the contact pad is configured for connection external to the device by a bond wire attached thereto.

35. (New Claim) The integrated circuit device of claim 30 wherein contact pad is configured for connection external to the device by a solder bump attached thereto.

36. (New Claim) The integrated circuit device of claim 30 wherein a material of the metallization interconnect system comprises copper and a material of the contact pad and second interconnect structure comprises aluminum, and further including a barrier material located between the copper and the aluminum in regions where the second interconnect structure is in contact with the second interconnect feature.

37. (New Claim) The integrated circuit device of claim 30 wherein the metallization interconnect system further comprises substantially horizontal conductive runners and substantially vertical conductive vias interconnecting overlying and underlying conductive runners.

38. (New Claim) The integrated circuit device of claim 30 further comprising a dielectric feature disposed between at least a portion of the second interconnect structure and the dielectric layer.

39. (New Claim) An integrated circuit device comprising:
a metallization interconnect system located over a substrate, the metallization interconnect system including first and second interconnect features located within a dielectric layer;

a plurality of contact pads disposed over the metallization interconnect system, one or more of the plurality of contact pads configured for connection external to the device;

a second interconnect structure forming a single conductive feature with at least one of the plurality of contact pads and in contact with the second interconnect feature; and

a passivation layer overlying at least a portion of the second interconnect structure.

40. (New Claim) The integrated circuit device of claim 39 wherein the second interconnect structure is a power bus.

41. (New Claim) The integrated circuit device of claim 39 wherein a plane of an upper surface of the contact pad is not coplanar with a plane of an upper surface of the second interconnect structure

42. (New Claim) The integrated circuit device of Claim 41 wherein the plane of the second interconnect structure is above the plane of the contact pad.

43. (New Claim) The integrated circuit device of claim 39 wherein the contact pad is configured for connection external to the device by a bond wire attached thereto.

44. (New Claim) The integrated circuit device of claim 39 wherein contact pad is configured for connection external to the device by a solder bump attached thereto.

45. (New Claim) The integrated circuit device of claim 39 wherein a material of the metallization interconnect system comprises copper and a material of the contact pad and second interconnect structure comprises aluminum, and further including a barrier material located between the copper and the aluminum in regions where the second interconnect structure is in contact with the second interconnect feature.

46. (New Claim) The integrated circuit device of claim 39 wherein the metallization interconnect system further comprises substantially horizontal conductive runners and substantially vertical conductive vias interconnecting overlying and underlying conductive runners.

47. (New Claim) The integrated circuit device of claim 39 further comprising a dielectric feature disposed between at least a portion of the second interconnect structure and the dielectric layer.